

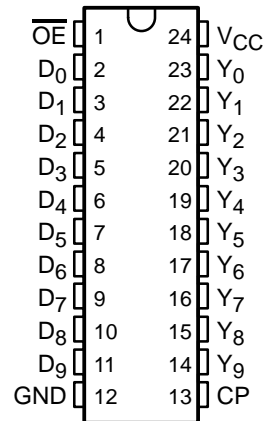
# CY74FCT821T

## 10-BIT BUS-INTERFACE REGISTER WITH 3-STATE OUTPUTS

SCCS033B– MAY 1994 – REVISED NOVEMBER 2001

- Function, Pinout, and Drive Compatible With FCT, F Logic, and AM29821
- Reduced  $V_{OH}$  (Typically = 3.3 V) Version of Equivalent FCT Functions
- Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics
- $I_{off}$  Supports Partial-Power-Down Mode Operation
- Matched Rise and Fall Times
- Fully Compatible With TTL Input and Output Logic Levels
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)
- 64-mA Output Sink Current  
32-mA Output Source Current
- High-Speed Parallel Register With Positive-Edge-Triggered D-Type Flip-Flops
- 3-State Outputs

P, Q, OR SO PACKAGE  
(TOP VIEW)



### description

This bus-interface register is designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider address/data paths or buses carrying parity. The CY74FCT821T is a 10-bit-wide buffered version of the popular CY74FCT374 function. This device is ideal for use as an output port requiring high  $I_{OL}/I_{OH}$ .

This device is designed for high-capacitance load drive capability, while providing low-capacitance bus loading at both inputs and outputs. Outputs are designed for low-capacitance bus loading in the high-impedance state.

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

PIN DESCRIPTION

NAME	I/O	DESCRIPTION
D	I	D flip-flop data inputs
CP	O	Clock pulse for the register. Enters data into the register on the low-to-high clock transition.
Y	O	Register 3-state outputs
$\overline{OE}$	I	Output control. When $\overline{OE}$ is high, the Y outputs are in the high-impedance state. When $\overline{OE}$ is low, true register data is present at the Y outputs.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS  
INSTRUMENTS**

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CY74FCT821T

10-BIT BUS-INTERFACE REGISTER

WITH 3-STATE OUTPUTS

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ORDERING INFORMATION

T <sub>A</sub>	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	QSOP – Q	Tape and reel	6	CY74FCT821CTQCT	FCT821C
	SOIC – SO	Tube	6	CY74FCT821CTSOC	FCT821C
		Tape and reel	6	CY74FCT821CTSOCT	
	DIP – P	Tube	7.5	CY74FCT821BTPC	CY74FCT821BTPC
	SOIC – SO	Tube	7.5	CY74FCT821BTSOC	FCT821B
		Tape and reel	7.5	CY74FCT821BTSOCT	
	QSOP – Q	Tape and reel	10	CY74FCT821ATQCT	FCT821A
	SOIC – SO	Tube	10	CY74FCT821ATSOC	FCT821A
		Tape and reel	10	CY74FCT821ATSOCT	

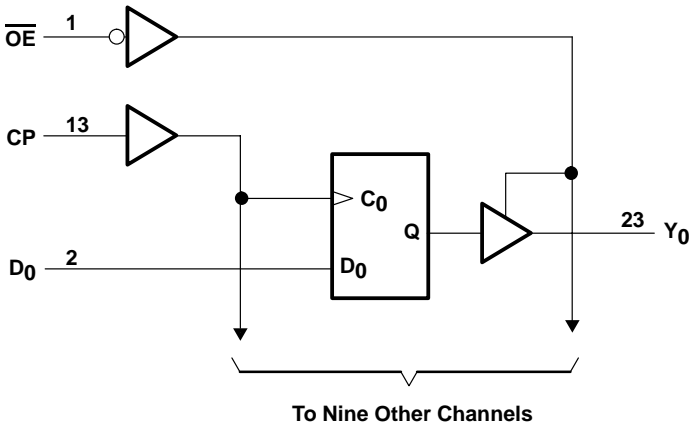
† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at [www.ti.com/sc/package](http://www.ti.com/sc/package).

FUNCTION TABLE

INPUTS			INTERNAL OUTPUTS		FUNCTION
$\overline{OE}$	D	CP	Q	Y	
H	X	↑	L	Z	Z
H	L	↑	L	Z	Load
H	H	↑	H	Z	
L	L	↑	L	L	
L	H	↑	H	H	

H = High logic level, L = Low logic level, X = Don't care,  
↑ = Low-to-high transition, Z = High-impedance state

logic diagram (positive logic)



**CY74FCT821T**  
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**absolute maximum rating over operating free-air temperature range (unless otherwise noted)<sup>†</sup>**

Supply voltage range to ground potential .....	–0.5 V to 7 V
DC input voltage range .....	–0.5 V to 7 V
DC output voltage range .....	–0.5 V to 7 V
DC output current (maximum sink current/pin) .....	120 mA
Package thermal impedance, $\theta_{JA}$ (see Note 1): P package .....	67°C/W
(see Note 2): Q package .....	61°C/W
(see Note 2): SO package .....	46°C/W
Ambient temperature range with power applied, $T_A$ .....	–65°C to 135°C
Storage temperature range, $T_{stg}$ .....	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The package thermal impedance is calculated in accordance with JESD 51-3.  
2. The package thermal impedance is calculated in accordance with JESD 51-7.

**recommended operating conditions (see Note 3)**

	MIN	NOM	MAX	UNIT
$V_{CC}$ Supply voltage	4.75	5	5.25	V
$V_{IH}$ High-level input voltage	2			V
$V_{IL}$ Low-level input voltage			0.8	V
$I_{OH}$ High-level output current			–32	mA
$I_{OL}$ Low-level output current			64	mA
$T_A$ Operating free-air temperature	–40		85	°C

NOTE 3: All unused inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation.

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## 10-BIT BUS-INTERFACE REGISTER

### WITH 3-STATE OUTPUTS

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**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V <sub>IK</sub>	V <sub>CC</sub> = 4.75 V,	I <sub>IN</sub> = −18 mA		−0.7	−1.2	V
V <sub>OH</sub>	V <sub>CC</sub> = 4.75 V	I <sub>OH</sub> = −32 mA	2		V	
		I <sub>OH</sub> = −15 mA	2.4	3.3		
V <sub>OL</sub>	V <sub>CC</sub> = 4.75 V,	I <sub>OL</sub> = 64 mA		0.3	0.55	V
V <sub>hys</sub>	All inputs			0.2		V
I <sub>I</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> = V <sub>CC</sub>			5	μA
I <sub>IH</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> = 2.7 V			±1	μA
I <sub>IL</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> = 0.5 V			±1	μA
I <sub>OZH</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 2.7 V			10	μA
I <sub>OZL</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 0.5 V			−10	μA
I <sub>OS</sub> ‡	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 0 V	−60	−120	−225	mA
I <sub>off</sub>	V <sub>CC</sub> = 0 V,	V <sub>OUT</sub> = 4.5 V			±1	μA
I <sub>CC</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> ≤ 0.2 V, V <sub>IN</sub> ≥ V <sub>CC</sub> − 0.2 V		0.1	0.2	mA
ΔI <sub>CC</sub>	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> = 3.4 V§, f <sub>1</sub> = 0, Outputs open			0.5	2	mA
I <sub>CCD</sub> ¶	V <sub>CC</sub> = 5.25 V, One bit switching at 50% duty cycle, Outputs open, OE = EN = GND, V <sub>IN</sub> ≤ 0.2 V or V <sub>IN</sub> ≥ V <sub>CC</sub> − 0.2 V			0.06	0.12	mA/MHz
I <sub>C</sub> #	V <sub>CC</sub> = 5.25 V, Outputs open, OE = EN = GND	One bit switching at f <sub>1</sub> = 5 MHz at 50% duty cycle	V <sub>IN</sub> ≤ 0.2 V or V <sub>IN</sub> ≥ V <sub>CC</sub> − 0.2 V	0.7	1.4	mA
			V <sub>IN</sub> = 3.4 V or GND	1.2	3.4	
		Eight bits switching at f <sub>1</sub> = 2.5 MHz at 50% duty cycle	V <sub>IN</sub> ≤ 0.2 V or V <sub>IN</sub> ≥ V <sub>CC</sub> − 0.2 V	1.6	3.2	
			V <sub>IN</sub> = 3.4 V or GND	3.9	12.2	
C <sub>i</sub>				5	10	pF
C <sub>o</sub>				9	12	pF

† Typical values are at  $V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$ .

‡ Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests,  $I_{OS}$  tests should be performed last.

§ Per TTL-driven input ( $V_{IN} = 3.4\text{ V}$ ); all other inputs at  $V_{CC}$  or GND

¶ This parameter is derived for use in total power-supply calculations.

#  $I_C = I_{CC} + \Delta I_{CC} \times D_H \times N_T + I_{CCD} (f_0/2 + f_1 \times N_1)$

Where:

$I_C$  = Total supply current

$I_{CC}$  = Power-supply current with CMOS input levels

$\Delta I_{CC}$  = Power-supply current for a TTL high input ( $V_{IN} = 3.4\text{ V}$ )

$D_H$  = Duty cycle for TTL inputs high

$N_T$  = Number of TTL inputs at  $D_H$

$I_{CCD}$  = Dynamic current caused by an input transition pair (HLH or LHL)

$f_0$  = Clock frequency for registered devices, otherwise zero

$f_1$  = Input signal frequency

$N_1$  = Number of inputs changing at  $f_1$

All currents are in milliamperes and all frequencies are in megahertz.

|| Values for these conditions are examples of the  $I_{CC}$  formula.



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**timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)**

PARAMETER			TEST LOAD	CY74FCT821AT		CY74FCT821BT		CY74FCT821CT		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
$t_w$	Pulse duration	CP	$C_L = 50 \text{ pF}$ , $R_L = 500 \Omega$	7		6		6		ns
$t_{su}$	Setup time, before $CP\uparrow$	Data	$C_L = 50 \text{ pF}$ , $R_L = 500 \Omega$	4		3		3		ns
$t_h$	Hold time, after $CP\uparrow$	Data	$C_L = 50 \text{ pF}$ , $R_L = 500 \Omega$	2		1.5		1.5		ns

**switching characteristics over operating free-air temperature range (see Figure 1)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST LOAD	CY74FCT821AT		CY74FCT821BT		CY74FCT821CT		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
$t_{PLH}$	CP	Y	$C_L = 50 \text{ pF}$ , $R_L = 500 \Omega$		10		7.5		6	ns
$t_{PHL}$					10		7.5		6	
$t_{PLH}$	CP	Y	$C_L = 300 \text{ pF}$ , $R_L = 500 \Omega$		20		15		12.5	ns
$t_{PHL}$					20		15		12.5	
$t_{PZH}$	$\overline{OE}$	Y	$C_L = 50 \text{ pF}$ , $R_L = 500 \Omega$		12		8		7	ns
$t_{PZL}$					12		8		7	
$t_{PZH}$	$\overline{OE}$	Y	$C_L = 300 \text{ pF}$ , $R_L = 500 \Omega$		23		15		12.5	ns
$t_{PZL}$					23		15		12.5	
$t_{PHZ}$	$\overline{OE}$	Y	$C_L = 5 \text{ pF}$ , $R_L = 500 \Omega$		7		6.5		6	ns
$t_{PLZ}$					7		6.5		6	
$t_{PHZ}$	$\overline{OE}$	Y	$C_L = 50 \text{ pF}$ , $R_L = 500 \Omega$		8		7.5		6.5	ns
$t_{PLZ}$					8		7.5		6.5	

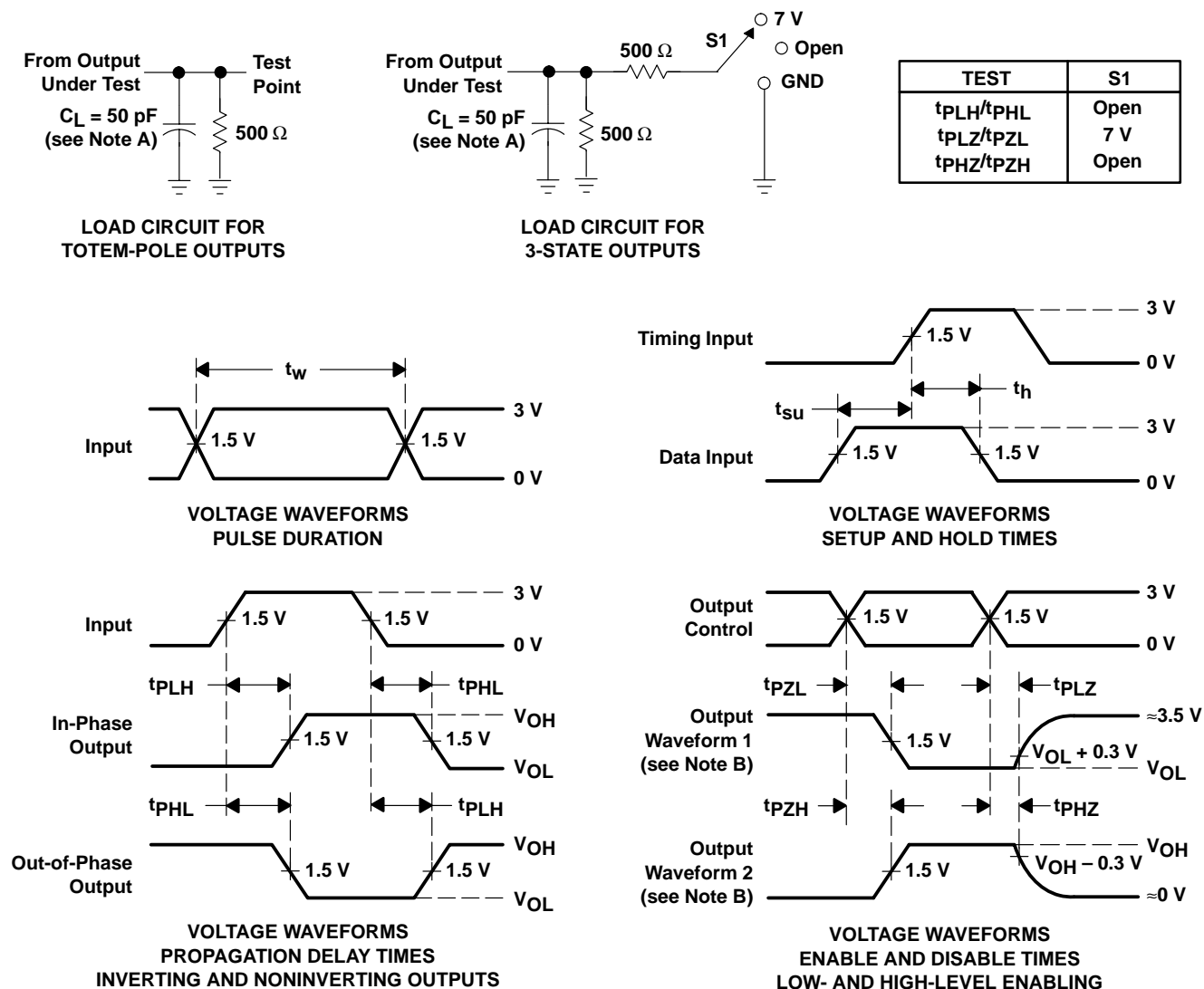
# CY74FCT821T

## 10-BIT BUS-INTERFACE REGISTER

### WITH 3-STATE OUTPUTS

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#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A.  $C_L$  includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

## PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">CY74FCT821ATSOC</a>	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821A
CY74FCT821ATSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821A
<a href="#">CY74FCT821BTSOC</a>	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821B
CY74FCT821BTSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821B
<a href="#">CY74FCT821CTQCT</a>	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT821C
CY74FCT821CTQCT.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT821C
<a href="#">CY74FCT821CTSOC</a>	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C
CY74FCT821CTSOC.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C
<a href="#">CY74FCT821CTSOCT</a>	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C
CY74FCT821CTSOCT.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C
CY74FCT821CTSOCTG4	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C
CY74FCT821CTSOCTG4.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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## TAPE AND REEL INFORMATION



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT821CTQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT821CTSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CY74FCT821CTSOCTG4	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT821CTQCT	SSOP	DBQ	24	2500	353.0	353.0	32.0
CY74FCT821CTSOCT	SOIC	DW	24	2000	350.0	350.0	43.0
CY74FCT821CTSOCTG4	SOIC	DW	24	2000	350.0	350.0	43.0

## TUBE

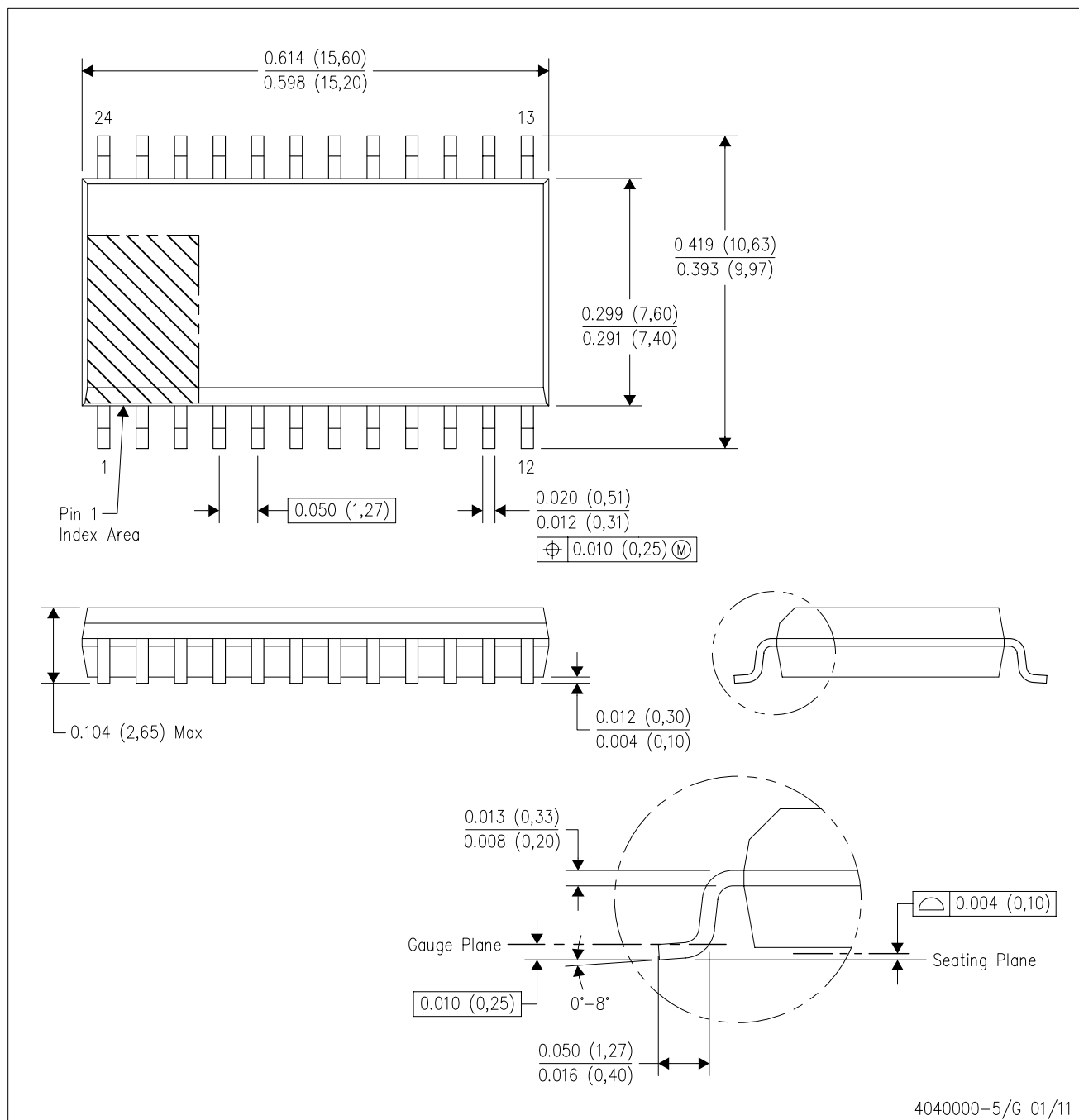


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
CY74FCT821ATSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821ATSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821BTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821BTSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821CTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821CTSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

DW (R-PDSO-G24)

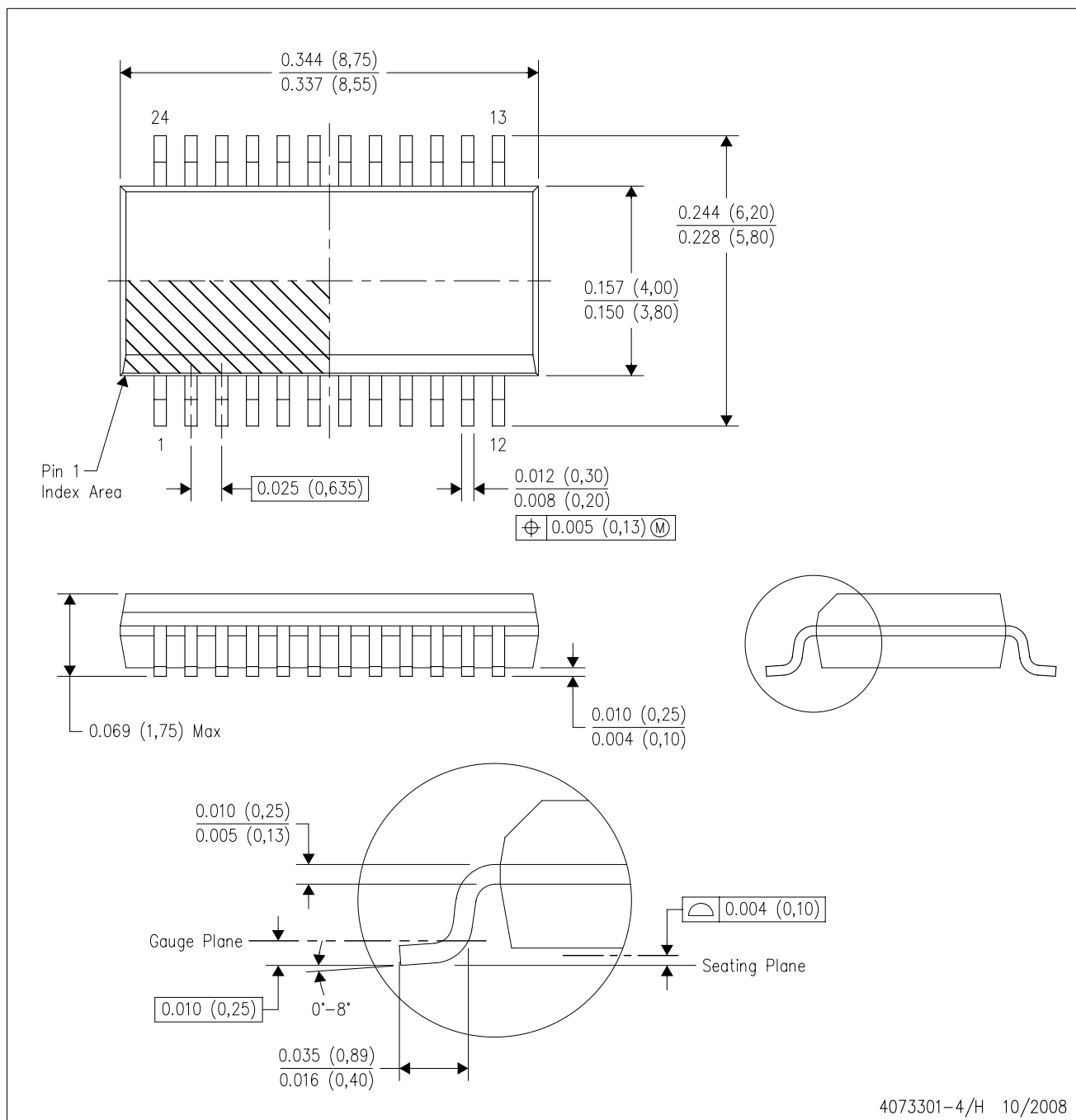
## PLASTIC SMALL OUTLINE



- NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.  
B. This drawing is subject to change without notice.  
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).  
D. Falls within JEDEC MS-013 variation AD.

DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
  - D. Falls within JEDEC MO-137 variation AE.

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